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AeroBase Group

View Online at https://aerobasegroup.com/nsn/5961-01-062-3485

Inclosure Material:

Metal

Overall Length:

0.280 inches

Overall Diameter:

Between 0.350 inches and 0.380 inches

Function For Which Designed:

Amplifier

Mounting Facility Quantity:

1

Internal Configuration:

Junction contact

Mounting Method:

Threaded stud

Features Provided:

Mounting hardware

Thread Size:

0.164 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

-36.0 breakdown voltage, collector-to-base, emitter open and -18.0 breakdown voltage, collector-to-emitter, base open and -4.0

breakdown voltage, emitter-to-base, collector open

Current Rating Per Characteristic:

10.00 milliamperes source cutoff current

Power Rating Per Characteristic:

75.0 watts small-signal input power, common-collector absolute

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Special Features:

Power output 40 watts; junction pattern arrangement: npn

Test Data Document:

08771-19a134060 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing,

etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Thread Series Designator:

Unc

Terminal Type And Quantity:

4 ribbon

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

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